

### Description

The LCE01P30 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications. It is ESD protected.

### General Features

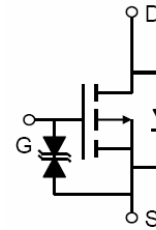
- $V_{DS} = -100V, I_D = -30A$   
 $R_{DS(ON)} < 58m\Omega @ V_{GS} = -10V$  (Typ: 50m $\Omega$ )
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance

### Application

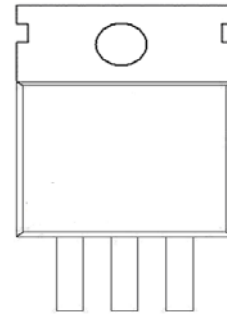
- Portable equipment and battery powered systems

**100% UIS TESTED!**

**100%  $\Delta V_d$ s TESTED!**



Schematic diagram



Marking and pin assignment



TO-220-3L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE01P30	LCE01P30	TO-220-3	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-30	A
Drain Current-Continuous ( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	-21	A
Pulsed Drain Current	$I_{DM}$	-120	A
Maximum Power Dissipation	$P_D$	120	W
Derating factor		0.8	W/ $^\circ C$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

**Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta jc}$	1.25	$^{\circ}C/W$
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**Electrical Characteristics ( $T_C=25^{\circ}C$  unless otherwise noted)**

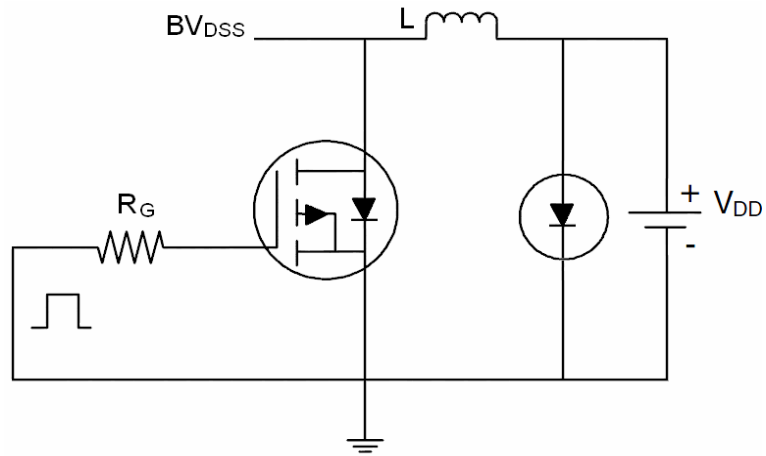
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.5	-1.9	-2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-15A$	-	50	58	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-50V, I_D=-10A$	5	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=-25V, V_{GS}=0V,$ $F=1.0MHz$	-	2700	-	PF
Output Capacitance	$C_{oss}$		-	790	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	450	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-50V, I_D=-15A$ $V_{GS}=-10V, R_{GEN}=9.1\Omega$	-	17	-	nS
Turn-on Rise Time	$t_r$		-	80	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	45	-	nS
Turn-Off Fall Time	$t_f$		-	65	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-50V, I_D=-15A,$ $V_{GS}=-10V$	-	90	-	nC
Gate-Source Charge	$Q_{gs}$		-	15	-	nC
Gate-Drain Charge	$Q_{gd}$		-	35	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=-10A$	-	-	-1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$	-	-	-	-30	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = -15A$ $di/dt = 100A/\mu s$ <sup>(Note 3)</sup>	-	90	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	70	-	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

**Notes:**

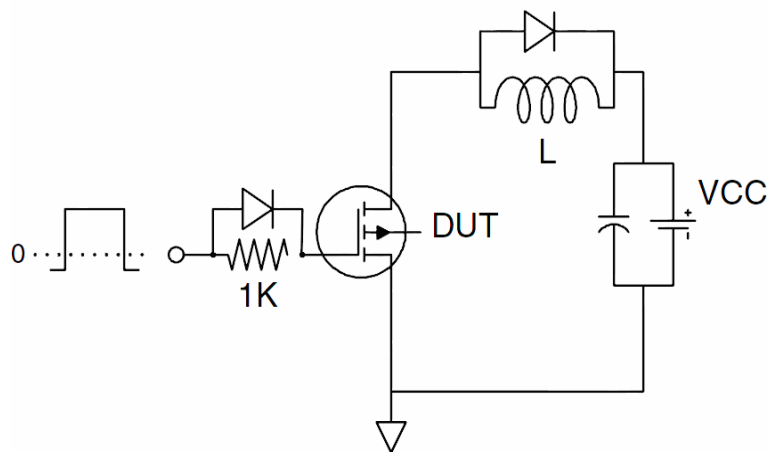
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^{\circ}C, V_{DD}=-50V, V_G=-10V, L=0.5mH, R_g=25\Omega$

**Test Circuit**

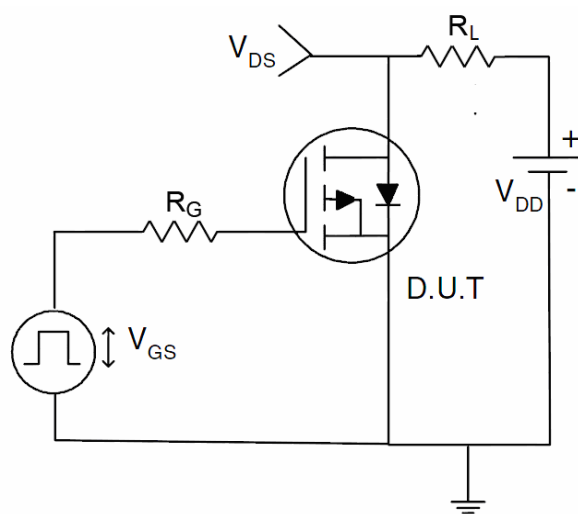
**1) E<sub>AS</sub> Test Circuit**



**2) Gate Charge Test Circuit**



**3) Switch Time Test Circuit**



Typical Electrical and Thermal Characteristics (Curves)

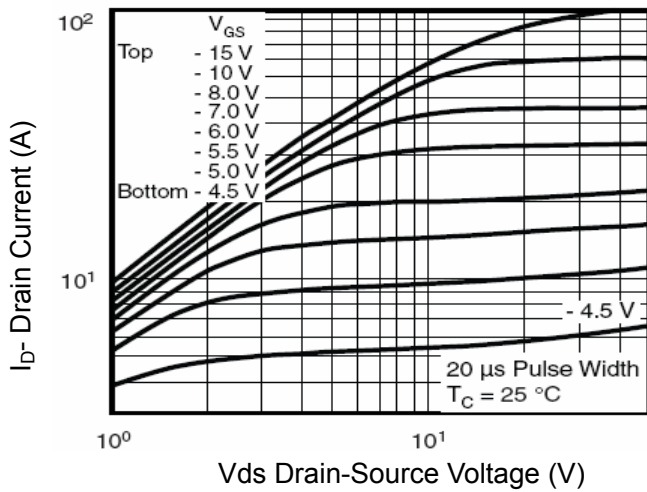


Figure 1 Output Characteristics

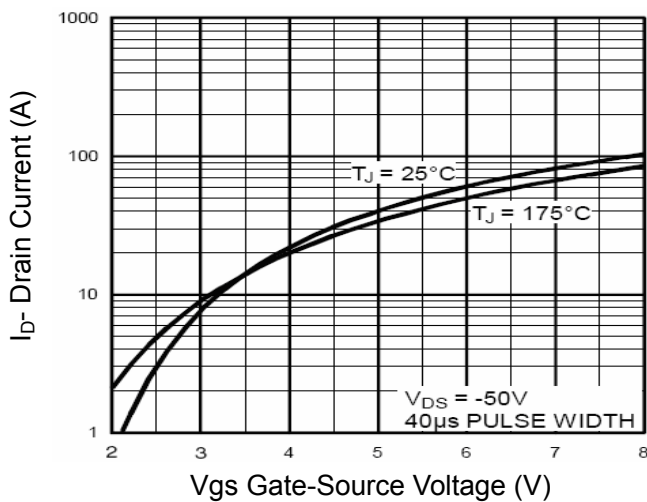


Figure 2 Transfer Characteristics

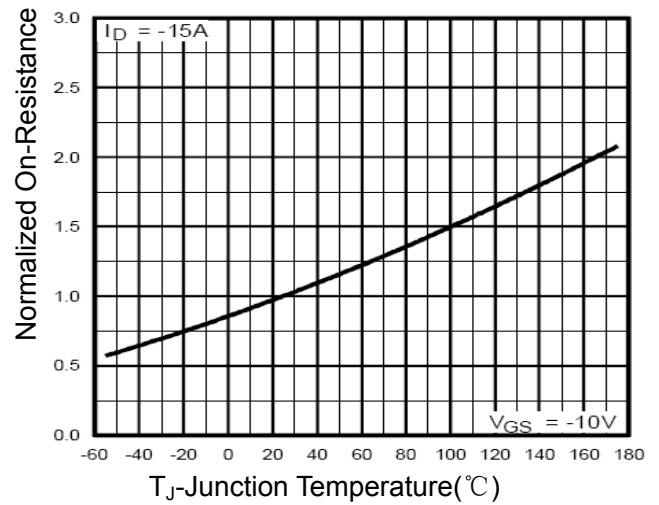


Figure 4 Rdson-Junction Temperature

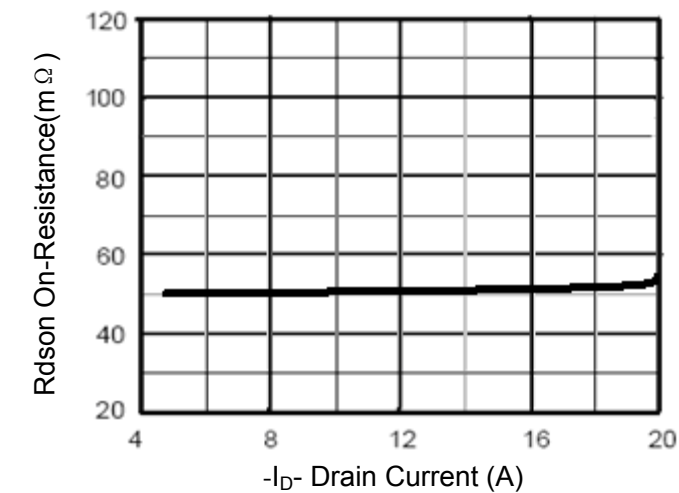


Figure 3 Rdson- Drain Current

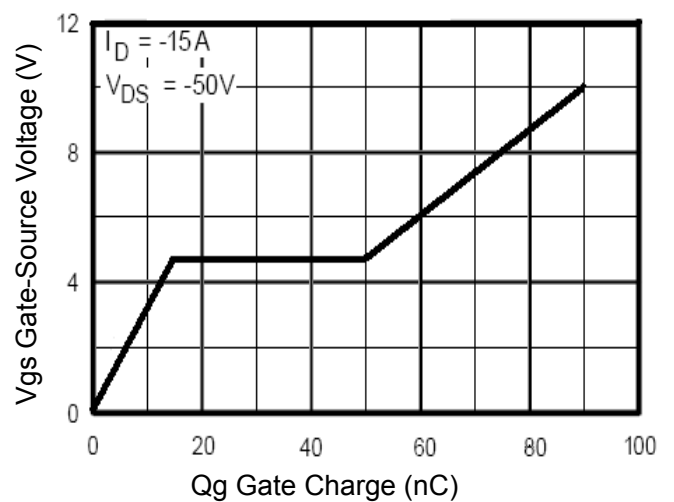


Figure 5 Gate Charge

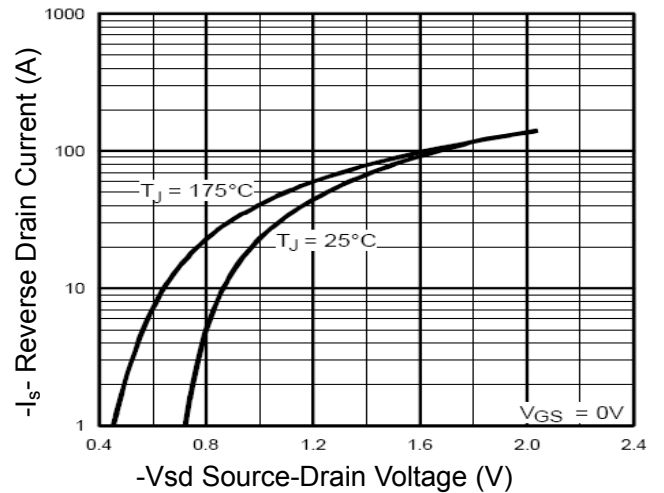


Figure 6 Source- Drain Diode Forward

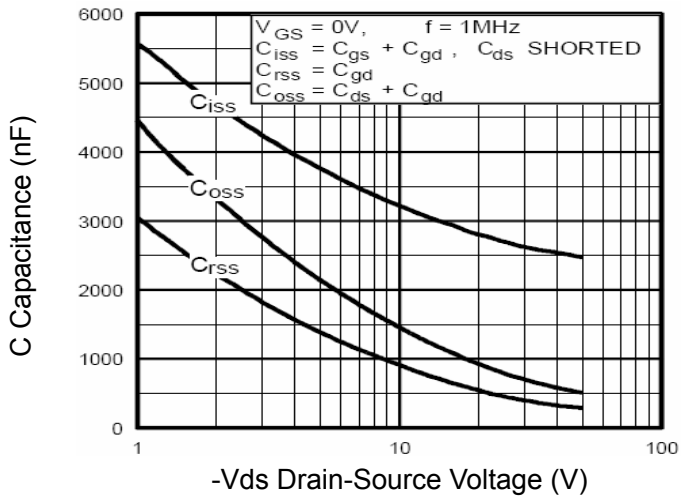


Figure 7 Capacitance vs Vds

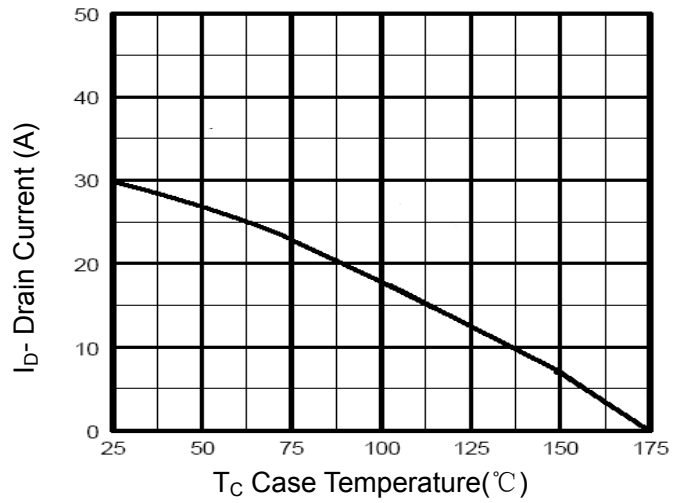


Figure 9 Drain Current vs Case Temperature

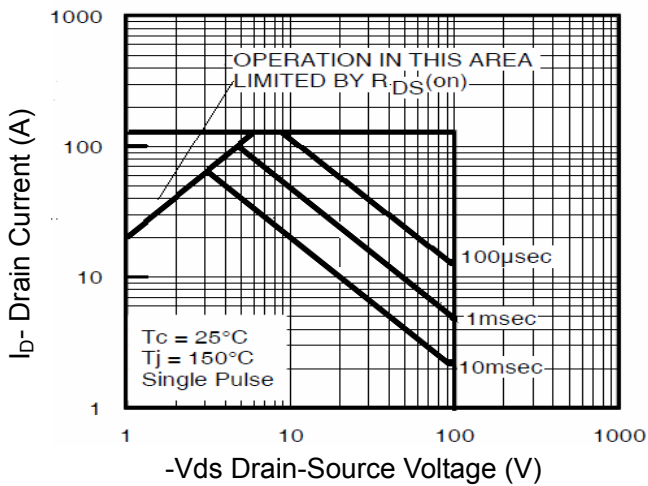


Figure 8 Safe Operation Area

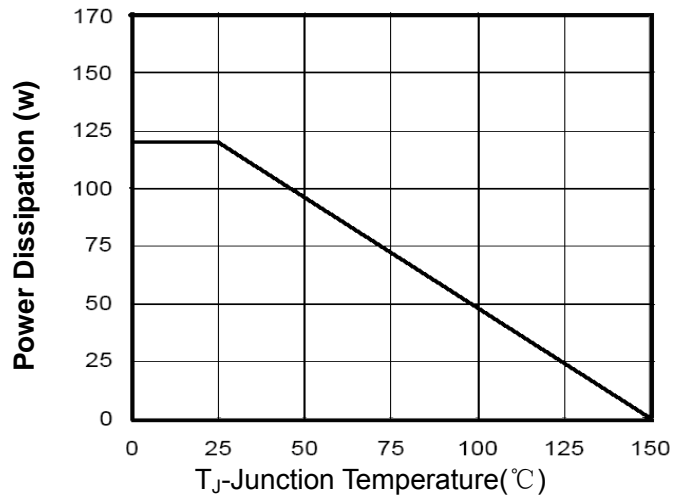


Figure 10 Power De-rating

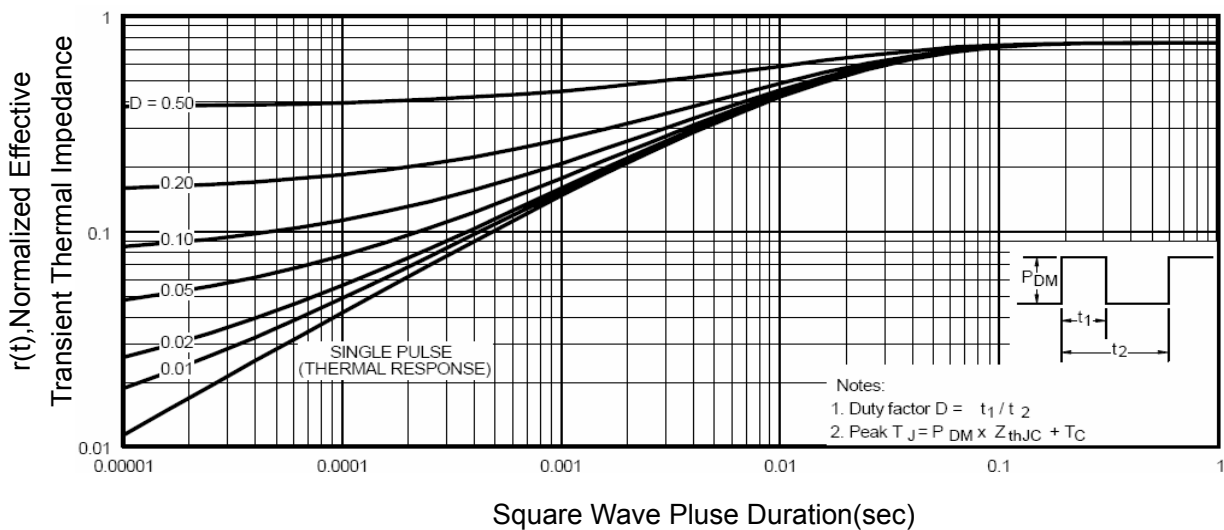
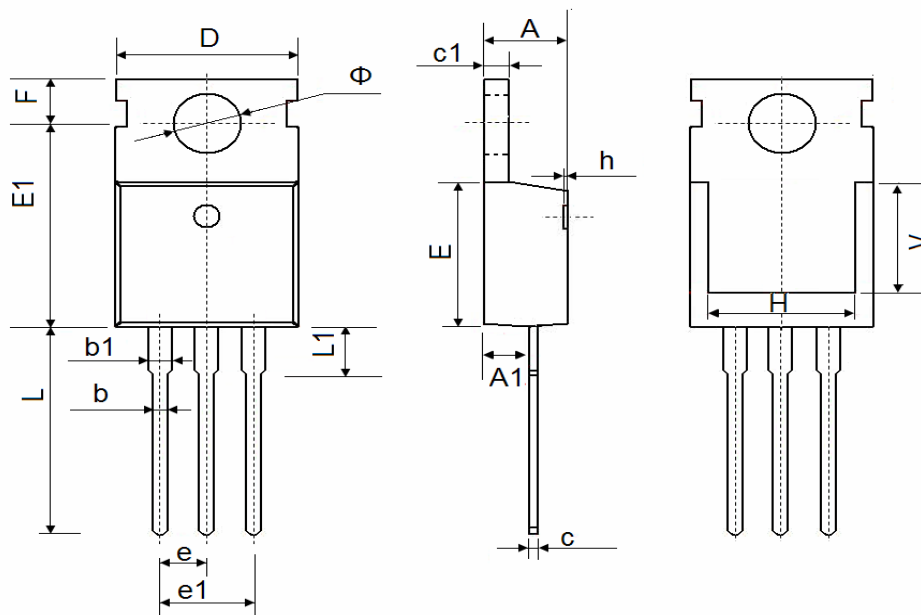


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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